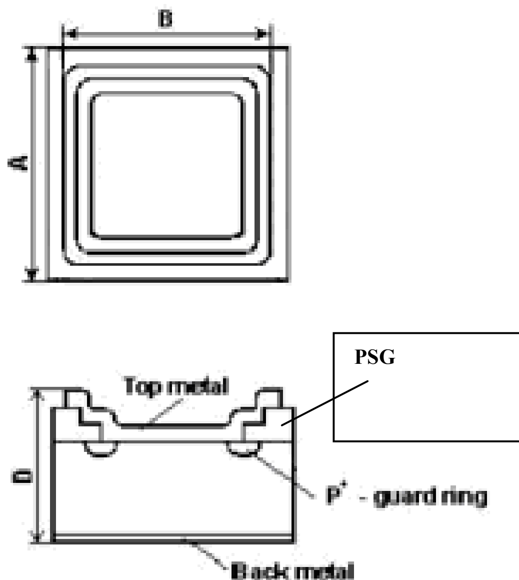
RoHS

SCHOTTKY DIODES. KDS-10040N.
PRELIMINARY

July. 2012

VSP-MIKRON	10A/40V. Die Size-90mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_B	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25˚C, I_F=10,0A	V_F	V	0,5	0,48
Maximum Reverse Current @ 25˚C, V_R=45V 25˚C, V_R=40V 100˚C, V_R=40V	I_R	MA	- 2,5 100,0	2,5 2,0 80,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	160	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	125	



DIM	ITEM	µm
A_X A_y	Die Size	2280 2280
B_X B_y	Top Metal Size	2140 2140
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;

b) ***Al-Ni-Ag*** – for Soldering.

Backside metal: ***Ti-Ni-Ag***.

www.vsp-mikron.com